

Supporting Information

Eu-doped ZnO quantum dots with solid-state fluorescence and dual emission for high-performance luminescent solar concentrators

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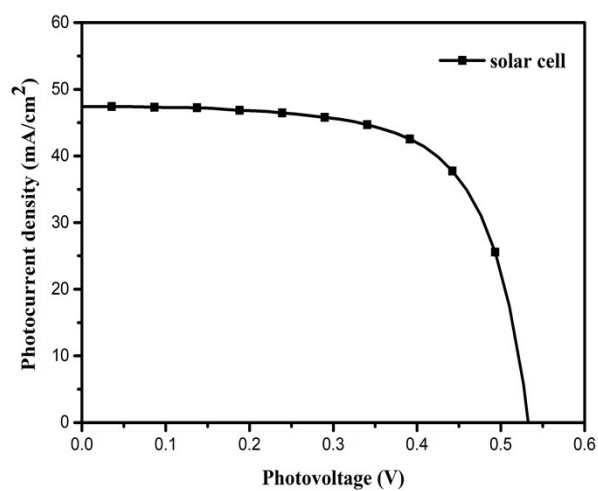


Figure S1. *J-V* curve of the Si solar cell under 1 sun.

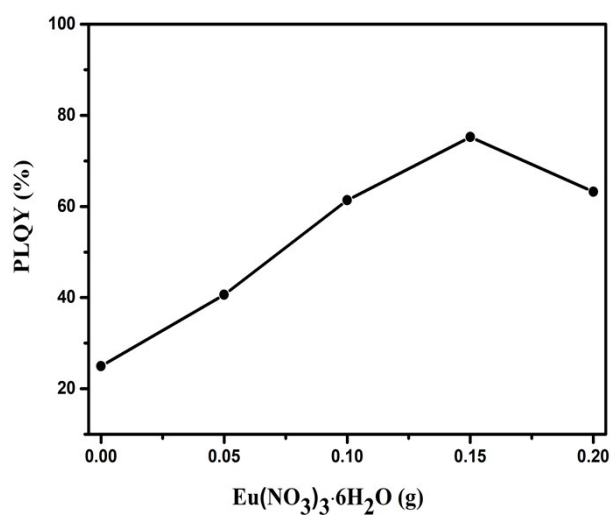


Figure S2. PLQY of Eu-doped ZnO QDs as a function of different concentration of Eu(NO₃)₃·6H₂O (excitation wavelength at 395 nm).

Table S1. Photovoltaic parameters of ZnO QDs/PVP thin-film LSCs.

Pure ZnO QDs (wt%)	I_{sc} (mA)	V_{oc} (V)	Fill Factor (%)	η_{opt} (%)
13.2	2.12	0.45	55.54	1.11

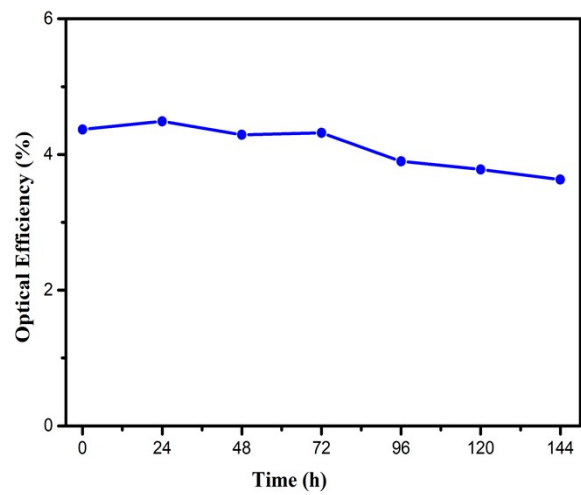


Figure S3. The stability of Eu-doped ZnO QDs LSC.